Consequence of Non-Uniform Expansion of InP-on-Si Wafers for the Performance of Buried Heterostructure Photonic Crystal Lasers - DTU Orbit (12/10/2019)

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E-beam metrology is employed to investigate the consequences of non-uniform expansion of 250nm InP layer bonded to Si substrate by BCB and direct wafer bonding for the performance of photonic crystal lasers with buried heterostructures.

General information
Publication status: Published
Organisations: Department of Photonics Engineering, Nanophotonic Devices, Centre of Excellence for Silicon Photonics for Optical Communications, Quantum and Laser Photonics, High-Speed Optical Communication
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Number of pages: 2
Publication date: 2018

Host publication Information
Title of host publication: Integrated Photonics Research, Silicon and Nanophotonics 2018
Publisher: Optical Society of America (OSA)
Article number: Paper ITh1B.4
ISBN (Print): 978-1-943580-43-9
DOIs: 10.1364/IPRSN.2018.ITh1B.4

Bibliographical note
From the session: Photonic Crystals and Nanocavities (ITh1B)
Source: PublicationPreSubmission
Source ID: 182559848
Research output: Chapter in Book/Report/Conference proceeding › Article in proceedings – Annual report year: 2019 › Research › peer-review